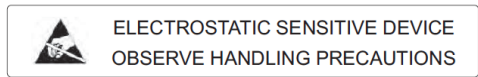


Features:

- Pass Band : 8.6G~ 10.0GHz
- Insertion Loss : 3.0dB
- Size : 13.65x5.0x0.5mm

Absolute Maximum Ratings

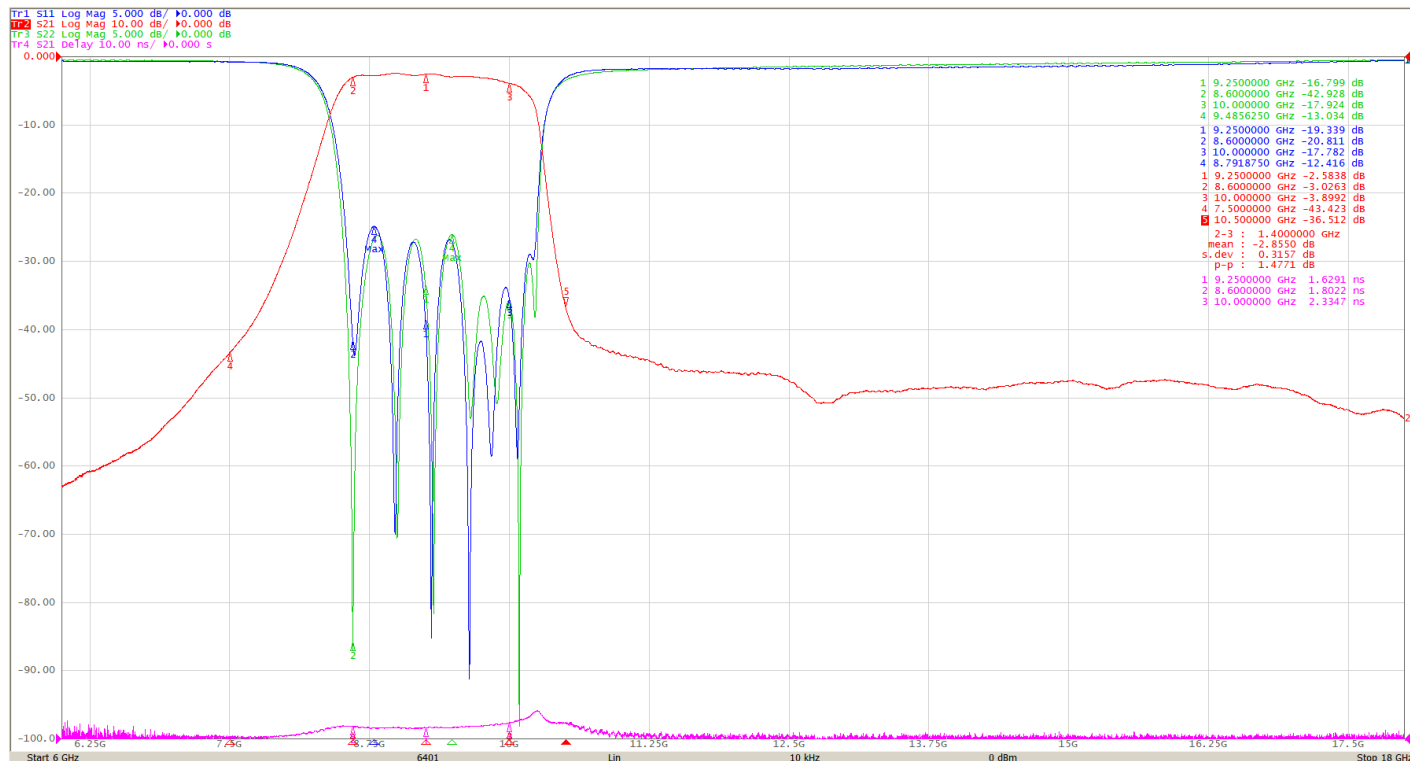
- Max. Input Power : +35dBm
- Storage Temperature : -55 ~ +85Deg.C
- Operating Temperature : -55 ~ +125Deg.C



Electrical Specifications (TA=+25Deg.C, 50Ω system)

Parameter	Min.Value	Typical Value	Max.Value	Unit
Frequency Range	8.6 ~ 10.0			GHz
Insertion Loss (Fc)		2.58	3.0	dB
Ripple		1.47	2.0	dB
Attenuation	DC~@7.5GHz	40	43.42	dB
	@10.5GHz	30	36.51	dB
Return Loss	12.0	12.41	-	dB
Group Delay		2.31	4.0	ns

Test Curve



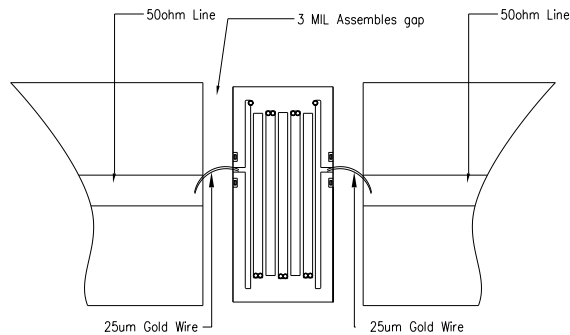
Size



Remarks: Unit : mm, Tolerance : ± 0.25 mm
 1. Chip bottom is gold plated and grounded.
 2. Bonding pressure points are gold plated.
 3. Don't bond on the through holes.

Applications

1. Assembly and Bonding Diagram. (Reference)



Assembly Diagram

2. The chip is back-metalized and can be die mounted with AuSn eutectic performs or with electrically conductive epoxy (for example ME8456).
3. The die should be assembled on carriers like Kovar or Mu-Cu which have same Coefficient of thermal expansion. (2.9ppm/°C) with Silicon, thickness 0.2mm max.
4. Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.
5. Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers.